Preferred Device

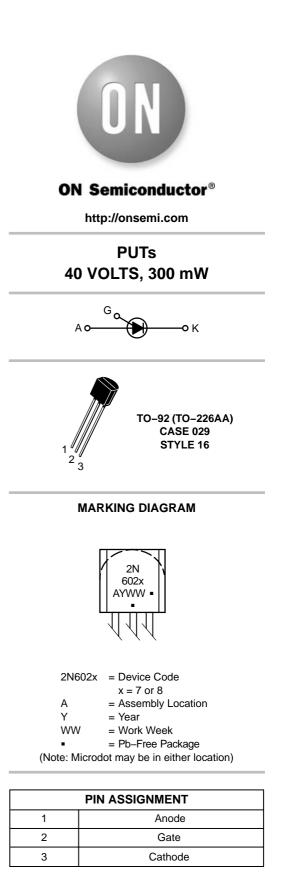
Programmable Unijunction Transistor

Programmable Unijunction Transistor Triggers

Designed to enable the engineer to "program" unijunction characteristics such as R_{BB} , η , I_V , and I_P by merely selecting two resistor values. Application includes thyristor-trigger, oscillator, pulse and timing circuits. These devices may also be used in special thyristor applications due to the availability of an anode gate. Supplied in an inexpensive TO-92 plastic package for high-volume requirements, this package is readily adaptable for use in automatic insertion equipment.

Features

- Programmable R_{BB} , η , I_V and I_P
- Low On–State Voltage 1.5 V Maximum @ $I_F = 50 \text{ mA}$
- Low Gate to Anode Leakage Current 10 nA Maximum
- High Peak Output Voltage 11 V Typical
- Low Offset Voltage 0.35 V Typical ($R_G = 10 \text{ k}\Omega$)
- Pb–Free Packages are Available*



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use

and hest overall value

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Semiconductor Components Industries, LLC, 2006 May, 2006 – Rev.6

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|-----------------------------------------------------------------------------------------------------------|-------------------------------------|-------------|-------------|
| Power Dissipation* Derate Above 25°C | P _F 1/θ _{JA} | 300 4.0 | mW mW/°C |
| DC Forward Anode Current* Derate Above 25°C | ١ _T | 150 2.67 | mA mA/°C |
| DC Gate Current* | I _G | ±50 | mA |
| Repetitive Peak Forward Current 100 μs Pulse Width, 1% Duty Cycle 20 μs Pulse Width, 1% Duty Cycle* | I _{TRM} | 1.0 2.0 | A |
| Non–Repetitive Peak Forward Current 10 μs Pulse Width | I _{TSM} | 5.0 | A |
| Gate to Cathode Forward Voltage* | V _{GKF} | 40 | V |
| Gate to Cathode Reverse Voltage* | V _{GKR} | -5.0 | V |
| Gate to Anode Reverse Voltage* | V _{GAR} | 40 | V |
| Anode to Cathode Voltage* (Note 1) | V _{AK} | ±40 | V |
| Capacitive Discharge Energy (Note 2) | E | 250 | μJ |
| Power Dissipation (Note 3) | PD | 300 | mW |
| Operating Temperature | T _{OPR} | -50 to +100 | °C |
| Junction Temperature | TJ | -50 to +125 | °C |
| Storage Temperature Range | T _{stg} | -55 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*Indicates JEDEC Registered Data 1. Anode positive, $R_{GA} = 1000 \Omega$ Anode negative, $R_{GA} = open$ 2. $E = 0.5 \cdot CV^2$ capacitor discharge energy limiting resistor and repetition. 3. Derate current and power above 25°C.

THERMAL CHARACTERISTICS

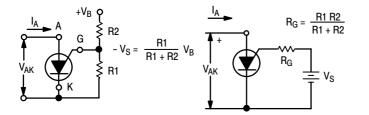
| Characteristic | Symbol | Max | Unit |
|-------------------------------------------------------------------------------------------|-----------------------|-----|------|
| Thermal Resistance, Junction-to-Case | $R_{	extsf{	heta}JC}$ | 75 | °C/W |
| Thermal Resistance, Junction-to-Ambient | R_{\thetaJA} | 200 | °C/W |
| Maximum Lead Temperature for Soldering Purposes (<1/16" from case, 10 seconds maximum) | ΤL | 260 | °C |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

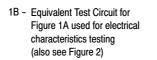
| Characteristic | | Fig. No. | Symbol | Min | Тур | Max | Unit |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------|----------|------------------|-----------------------------|----------------------------------|---------------------------|----------|
| Peak Current* (V _S = 10 Vdc, R _G = 1 MΩ) (V _S = 10 Vdc, R _G = 10 kΩ) | 2N6027 2N6028 2N6027 2N6028 | 2,9,11 | Ι _Ρ | - - - - | 1.25 0.08 4.0 0.70 | 2.0 0.15 5.0 1.0 | μΑ |
| Offset Voltage* ($V_S = 10 \text{ Vdc}, R_G = 1 \text{ M}\Omega$) ($V_S = 10 \text{ Vdc}, R_G = 10 \text{ k}\Omega$) | 2N6027 2N6028 (Both Types) | 1 | V _T | 0.2 0.2 0.2 | 0.70 0.50 0.35 | 1.6 0.6 0.6 | V |
| Valley Current* ($V_S = 10 \text{ Vdc}, R_G = 1 \text{ M}\Omega$) ($V_S = 10 \text{ Vdc}, R_G = 10 \text{ k} \Omega$) ($V_S = 10 \text{ Vdc}, R_G = 200 \Omega$) | 2N6027 2N6028 2N6027 2N6028 2N6027 2N6028 | 1,4,5 | Ι _V | - 70 25 1.5 1.0 | 18 18 150 150 - - | 50 25 - - - | μA mA |
| Gate to Anode Leakage Current* $(V_S = 40 \text{ Vdc}, T_A = 25^{\circ}\text{C}, \text{ Cathode Open})$ $(V_S = 40 \text{ Vdc}, T_A = 75^{\circ}\text{C}, \text{ Cathode Open})$ | | - | I _{GAO} | | 1.0 3.0 | 10 - | nAdc |
| Gate to Cathode Leakage Current (V _S = 40 Vdc, Anode to Cathode Shorted) | | - | I _{GKS} | - | 5.0 | 50 | nAdc |
| Forward Voltage* (I _F = 50 mA Peak) (Note 4) | | 1,6 | V _F | - | 0.8 | 1.5 | V |
| Peak Output Voltage* (V _G = 20 Vdc, C _C = 0.2 μ F) | | 3,7 | Vo | 6.0 | 11 | - | V |
| Pulse Voltage Rise Time (V _B = 20 Vdc, C _C = 0.2 μ F) | | 3 | t _r | - | 40 | 80 | ns |

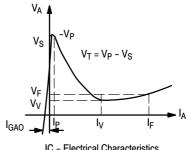
*Indicates JEDEC Registered Data

4. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.

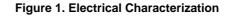


1A - Programmable Unijunction with "Program" Resistors R1 and R2





IC - Electrical Characteristics



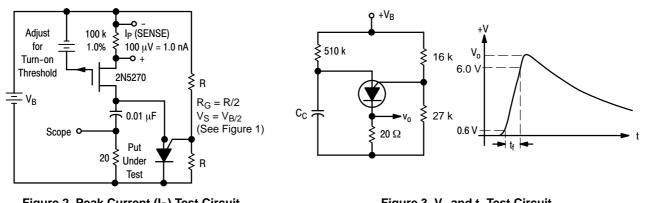


Figure 2. Peak Current (IP) Test Circuit

TYPICAL VALLEY CURRENT BEHAVIOR

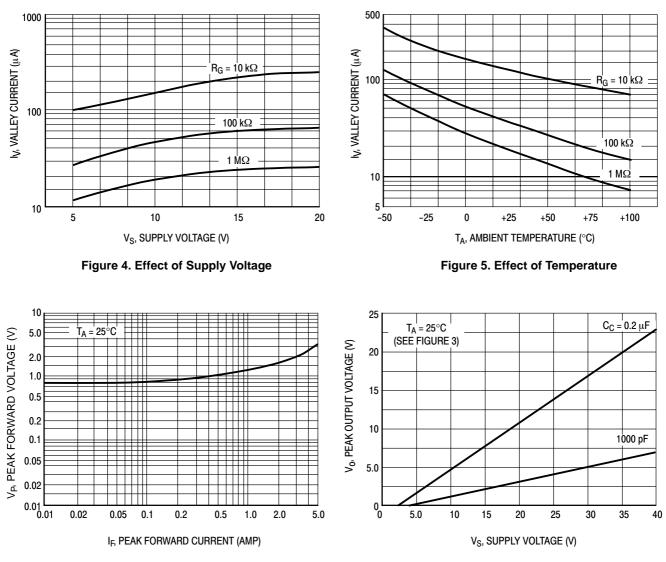
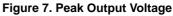
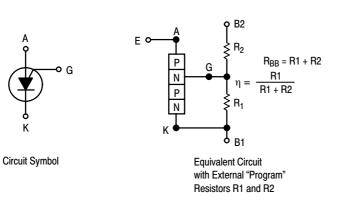


Figure 6. Forward Voltage





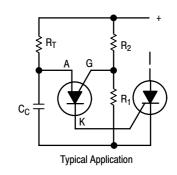
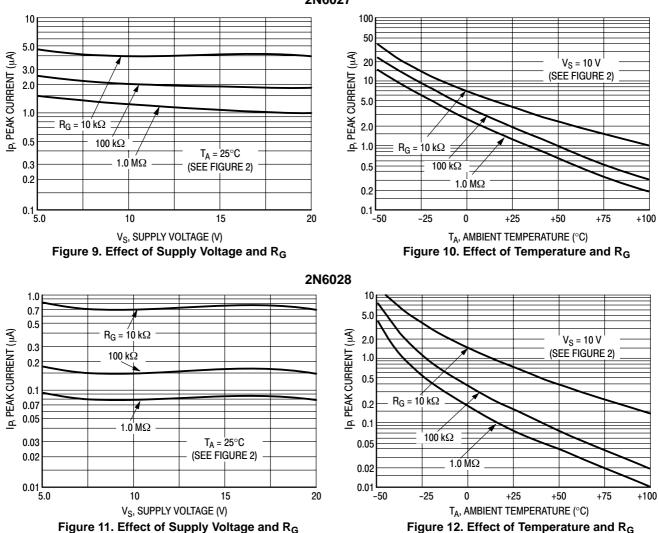


Figure 8. Programmable Unijunction

TYPICAL PEAK CURRENT BEHAVIOR

2N6027



ORDERING INFORMATION

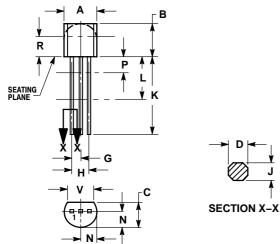
| U.S. | European Equivalent | Shipping [†] | Description of TO-92 Tape Orientation | | |
|-------------|---------------------|------------------------|-----------------------------------------------|--|--|
| 2N6027 | | | | | |
| 2N6027G | | | | | |
| 2N6028 | | 5000 Units / Box | N/A – Bulk | | |
| 2N6028G | | | | | |
| 2N6027RLRA | | | | | |
| 2N6027RLRAG | 2N6027RL1 | | | | |
| 2N6028RLRA | 2N6027RL1G | 2000 / Tape & Reel | Round side of TO–92 and adhesive tape visible | | |
| 2N6028RLRAG | | | | | |
| 2N6028RLRM | | | | | |
| 2N6028RLRMG | | 2000 / Tong & Amma Day | Flat side of TO–92 and adhesive tape visible | | |
| 2N6028RLRP | | 2000 / Tape & Ammo Box | Round side of TO 02 and adhesive tang visible | | |
| 2N6028RLRPG | | | Round side of TO–92 and adhesive tape visible | | |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*The "G" suffix indicates Pb-Free package available.

PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 029-11 **ISSUE AL**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 1.
- 2.
- CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R 3.
- IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND 4 BEYOND DIMENSION K MINIMUM

| | INC | HES | MILLIMETERS | | |
|-----|-------|-------|-------------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.175 | 0.205 | 4.45 | 5.20 | |
| В | 0.170 | 0.210 | 4.32 | 5.33 | |
| С | 0.125 | 0.165 | 3.18 | 4.19 | |
| D | 0.016 | 0.021 | 0.407 | 0.533 | |
| G | 0.045 | 0.055 | 1.15 | 1.39 | |
| Н | 0.095 | 0.105 | 2.42 | 2.66 | |
| J | 0.015 | 0.020 | 0.39 | 0.50 | |
| Κ | 0.500 | | 12.70 | | |
| L | 0.250 | | 6.35 | | |
| Ν | 0.080 | 0.105 | 2.04 | 2.66 | |
| Р | | 0.100 | | 2.54 | |
| R | 0.115 | | 2.93 | | |
| V | 0.135 | | 3.43 | | |

PIN 1 ANODE

GATE 2. 3. CATHODE

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